

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	248	(gate adj electrode) with:between with (first adj gate adj (insulation or insulating) adj film) with (second adj gate adj (insulation or insulating) adj film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 11:49
L7	110	(gate adj electrode) near10 between near10 (first adj gate adj (insulation or insulating) adj film) with (second adj gate adj (insulation or insulating) adj film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 11:49
L8	81	(gate adj electrode) near10 between near10 (first adj gate adj (insulation or insulating) adj film) near10 (second adj gate adj (insulation or insulating) adj film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 11:49
L9	31	((gate adj electrode) near10 between near10 (first adj gate adj (insulation or insulating) adj film) near10 (second adj gate adj (insulation or insulating) adj film)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 11:50
L10	1786	(first adj (tft or (thin adj film adj transistor))) and (second adj (tft or (thin adj film adj transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 11:51
L11	1622	(first adj (tft or (thin adj film adj transistor))) same (second adj (tft or (thin adj film adj transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 11:51
L12	306	(first adj (tft or (thin adj film adj transistor))) same (second adj (tft or (thin adj film adj transistor))) same (gate adj (insulation or insulating or dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 11:51
L13	45	(first adj (tft or (thin adj film adj transistor))) same (second adj (tft or (thin adj film adj transistor))) same (first adj gate adj (insulation or insulating or dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 11:52
L14	38	(first adj (tft or (thin adj film adj transistor))) same (second adj (tft or (thin adj film adj transistor))) same (first adj gate adj (insulation or insulating or dielectric) adj film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 11:52

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L15	37	(first adj (tft or (thin adj film adj transistor))) same (second adj (tft or (thin adj film adj transistor))) same (first adj gate adj (insulation or insulating or dielectric) adj film) same (second adj gate adj (insulation or insulating or dielectric) adj film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 12:08
L16	1786	((first adj (tft or (thin adj film adj transistor))) and (second adj (tft or (thin adj film adj transistor))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 12:10
L17	663	((first adj (tft or (thin adj film adj transistor))) same (second adj (tft or (thin adj film adj transistor))). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 12:10
L18	3	((first adj (tft or (thin adj film adj transistor))) same_offset same (second adj (tft or (thin adj film adj transistor))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 12:12
L19	6	((first adj (tft or (thin adj film adj transistor))) near10 offset near10 (second adj (tft or (thin adj film adj transistor))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 12:32
L20	184	dogan:in:	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 12:24
L21	2579	(gate adj electrode) near5 between near5 (gate adj (insulation or insulating) adj film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 12:34
L22	4933	(gate adj electrode) near10 between near10 (gate adj (insulation or insulating) adj film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 12:34
L23	305	(gate adj electrode) near10 between near10 ((first or second) near gate adj (insulation or insulating) adj film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 12:34

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L24	2	(gate adj electrode) near10 between near10 ((first or second) near gate adj (insulation or insulating) adj film) same ((first or second) adj (tft or (thin adj film adj transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 12:37
L25	39	(gate adj electrode) near10 between near10 (gate adj (insulation or insulating) adj film) same ((first or second) adj (tft or (thin adj film adj transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 12:38
L26	25	(gate adj electrode) near10 between near10 (gate adj (insulation or insulating) adj film) with ((first or second) adj (tft or (thin adj film adj transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 12:39
L27	19	(gate adj electrode) near10 between near10 (gate adj (insulation or insulating) adj film) near10 ((first or second) adj (tft or (thin adj film adj transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 12:40
L28	17	(gate adj electrode) near5 between near5 (gate adj (insulation or insulating) adj film) near10 ((first or second) adj (tft or (thin adj film adj transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 12:43
L29	14	("20020179008" "20030124778" "20030151049" "20030170938" "5563440" "6306693" "6362030" "6462723" "6506642" "6528852" "6635505" "6646288" "6706544" "6781646").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/14 12:52
L30	2576	(first adj (tft or (thin adj film adj transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 12:52
L31	1786	(first adj (tft or (thin adj film adj transistor))) and (second adj (tft or (thin adj film adj transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 12:53
L32	100	(first adj (tft or (thin adj film adj transistor))) with (gate adj electrode) with (gate adj (insulation or insulating) adj film) with (second adj (tft or (thin adj film adj transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 12:54

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L33	10	(first adj (tft or (thin adj film adj transistor))) with (gate adj electrode) with (first adj gate adj (insulation or insulating) adj film) with (second adj (tft or (thin adj film adj transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 13:00
L34	22	(first adj (tft or (thin adj film adj transistor))) with (gate adj electrode) same (first adj gate adj (insulation or insulating) adj film) same (second adj (tft or (thin adj film adj transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 13:03
L35	26	(first adj (tft or (thin adj film adj transistor))) same (gate adj electrode) same (first adj gate adj (insulation or insulating) adj film) same (second adj (tft or (thin adj film adj transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 13:04
L36	78	(tft or (thin adj film adj transistor)) near5 (lower or upper or first or second) near (gate adj (insulating or insulation) adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 13:05
L37	298	(tft or (thin adj film adj transistor)) near5 (lower or upper or first or second) near (gate adj (insulating or insulation) adj (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 13:05
L38	304	(tft or (thin adj film adj transistor)) near5 ('lower or upper or first or second) near (gate adj (dielectric or insulating or insulation) adj (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 13:08